



Dual N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	30V
I_D	32A
$R_{DS(ON)}$ (at V	



YJQ3622BJ

Electrical Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Units
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Typical Electrical and Thermal Characteristic Diagrams

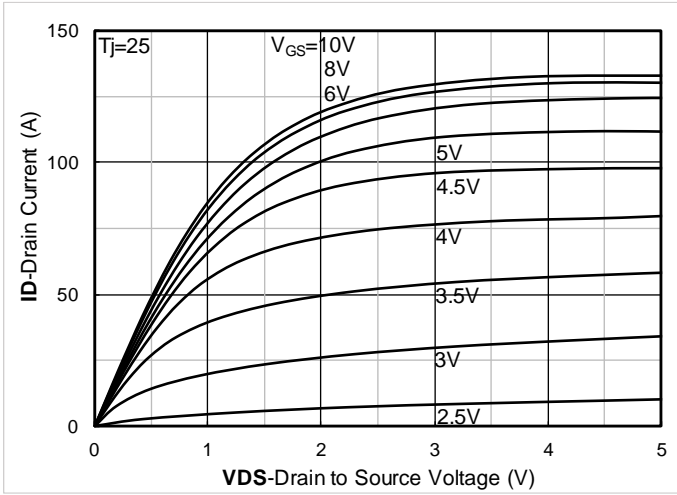


Figure 1. Output Characteristics; typical values

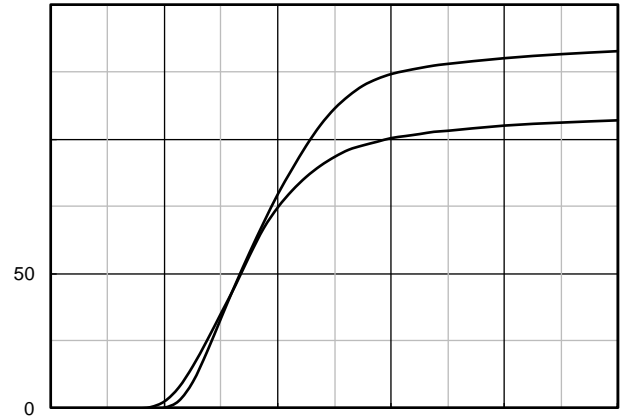


Figure 2. Transfer Characteristics; typical values

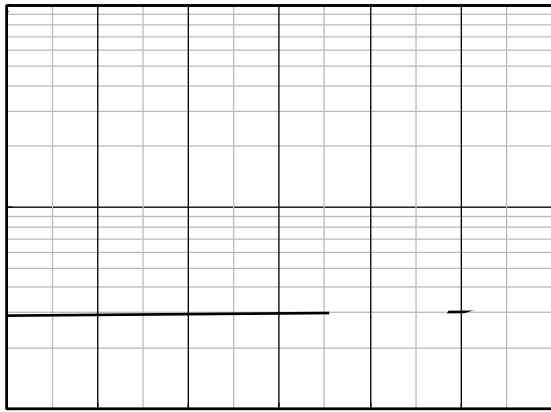


Figure 3. Capacitance Characteristics; typical value

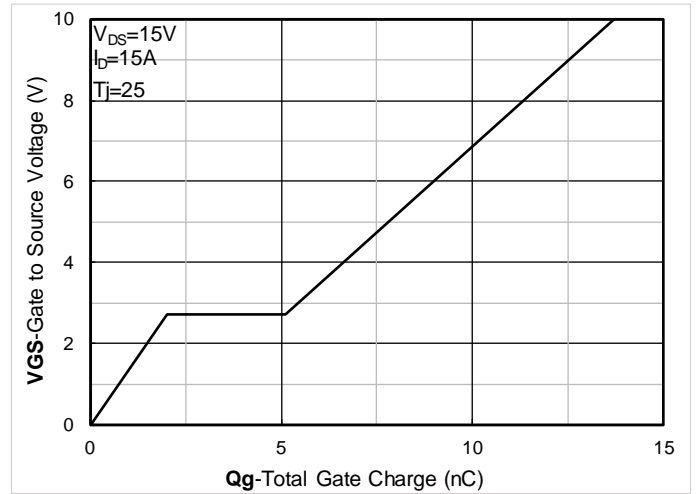


Figure 4. Gate Charge; typical values

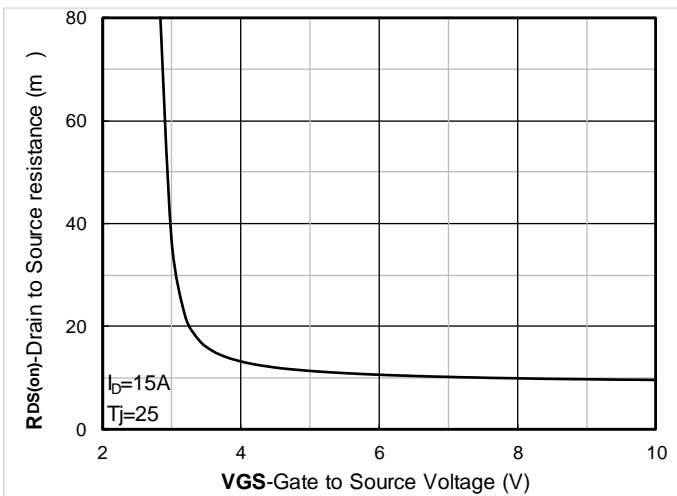


Figure 5. On-Resistance vs. Gate to Source Voltage; typical value

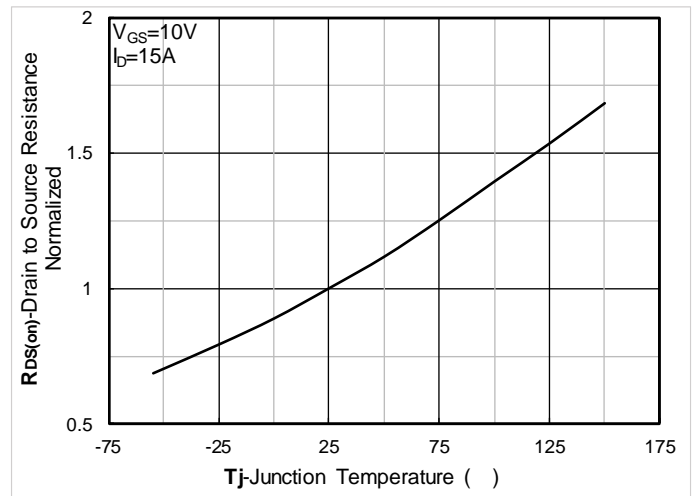
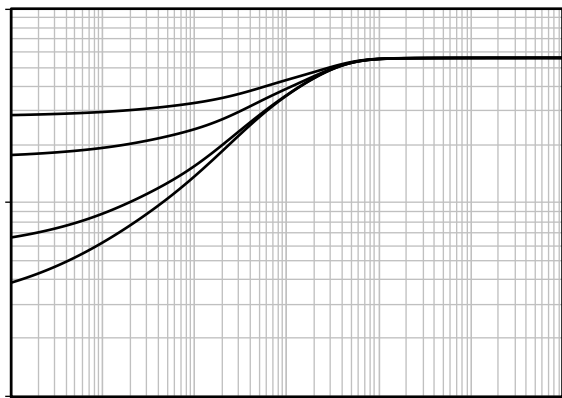


Figure 6. Normalized On-Resistance



Test Circuits & Waveforms

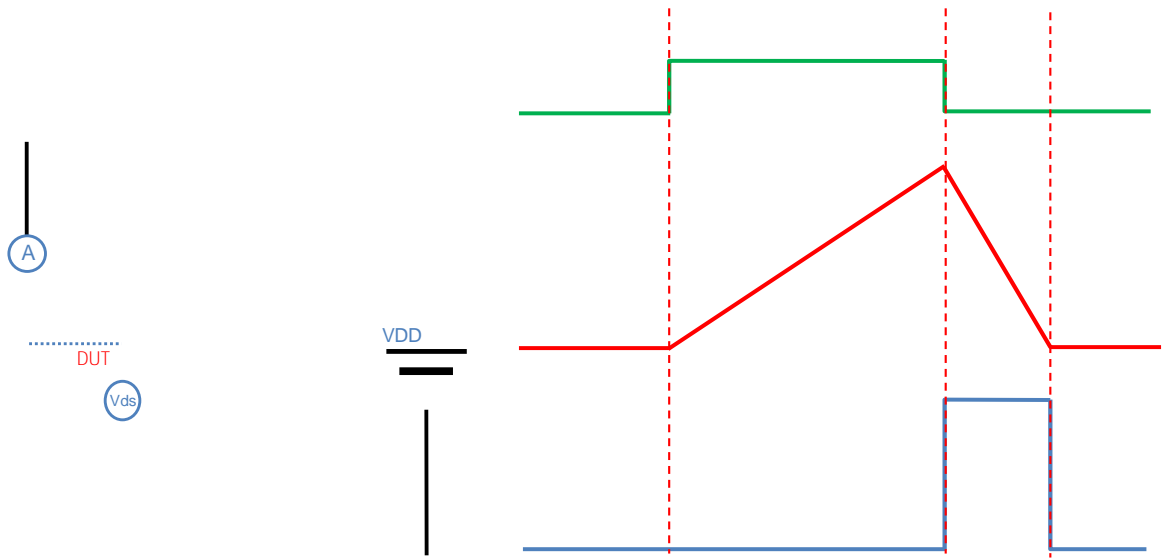


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

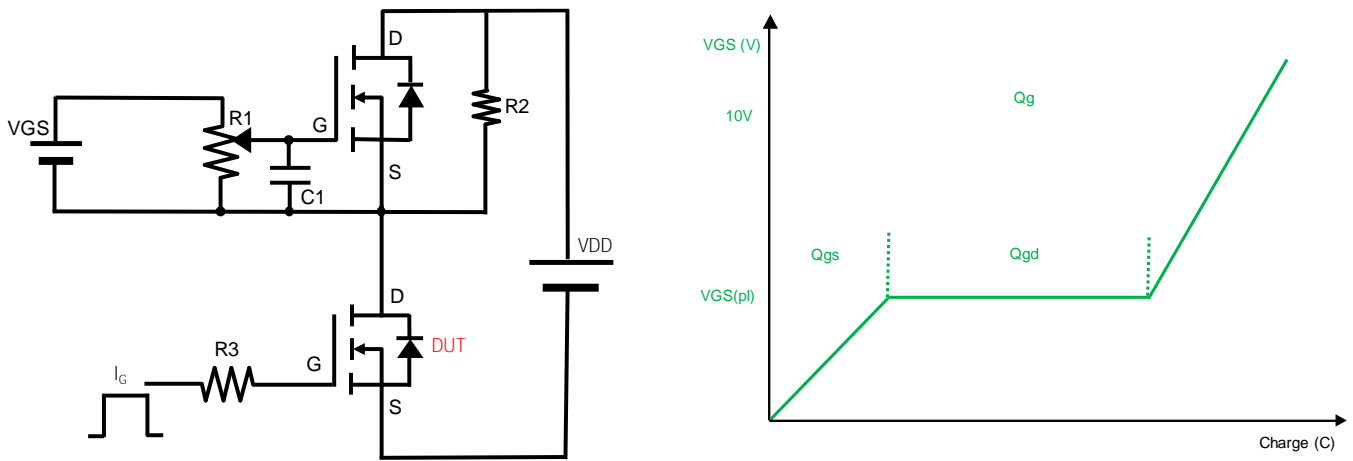


Figure B. Gate Charge Test Circuit & Waveform

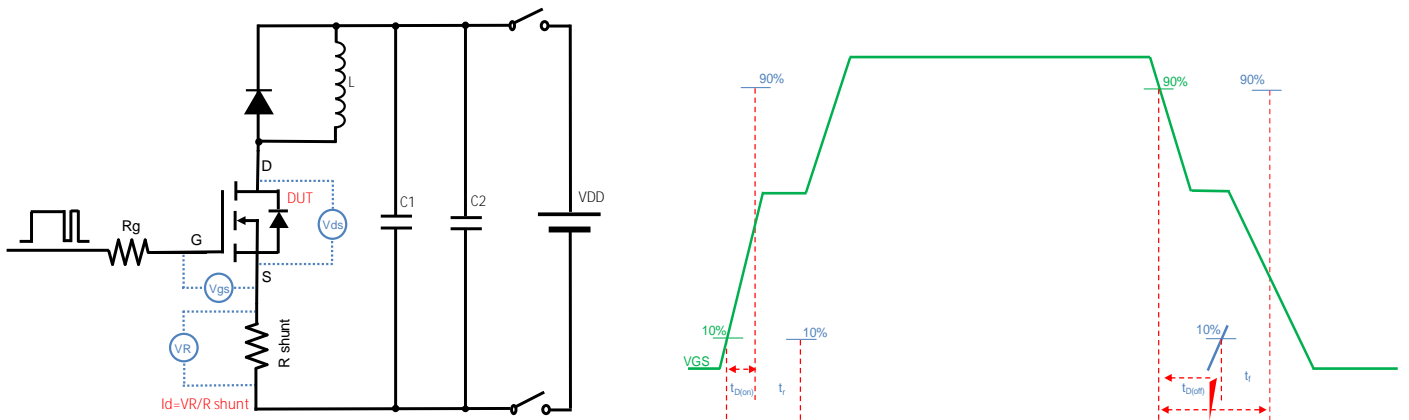


Figure C. Resistive Switching Test Circuit & Waveform

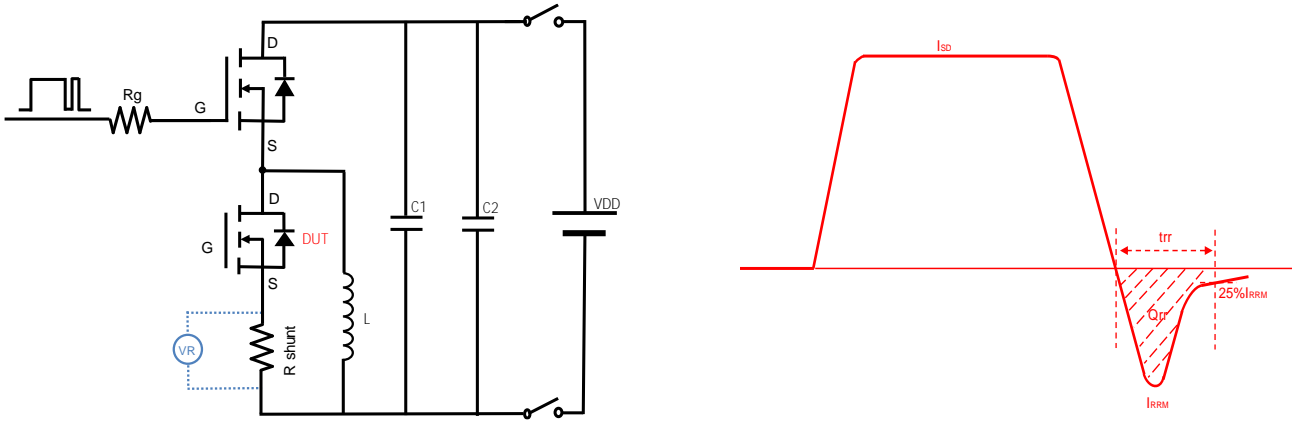
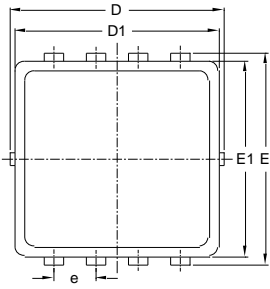


Figure D. Diode Recovery Test Circuit & Waveform

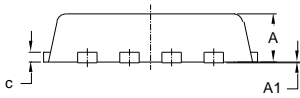


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PDFN3333-8L-Dual Package information



SYMBOL	DIMENSIONS			
	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.028	0.033	0.700	0.850
A1	0.000	0.002	0.000	0.050
b	0.008	0.016	0.200	0.400
c	0.004	0.010	0.100	0.250
D	0.124	0.136	3.150	3.450
D1	0.118	0.130	3.000	3.300
D2	0.033	0.049	0.840	1.240
D3	0.089	0.104	2.250	2.650
E	0.124	0.136	3.150	3.450
E1	0.114	0.126	2.93.029 Tm -0.00929 Tc[E1]]TJET2:	



UNIT mm NOTE:
1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.

1.840



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